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**FIG.1:**Power dissipation vs. on-state current (per thyristor or diode)

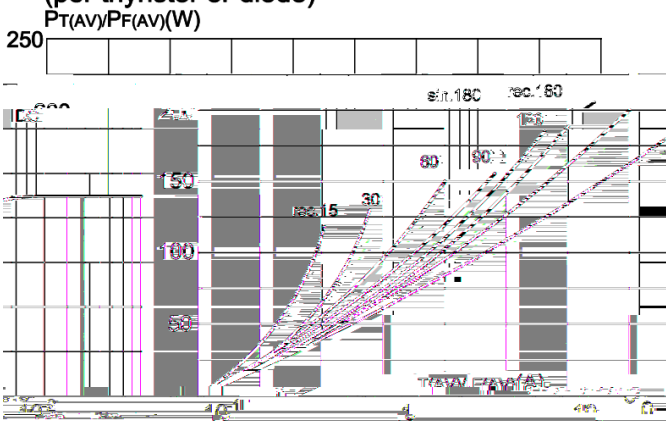



**FIG.2:** Maximum transient thermal impedance junction to case(per thyristor or diode)

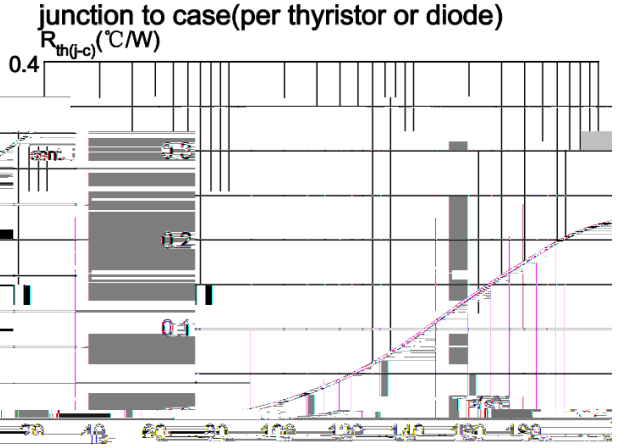



**FIG.3:**Forward characteristics (per thyristor or diode)

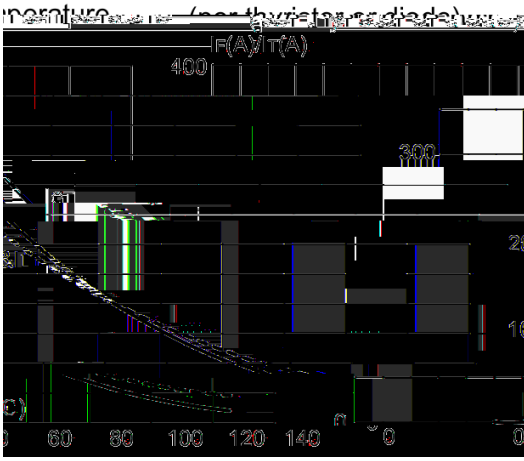



**FIG.4:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

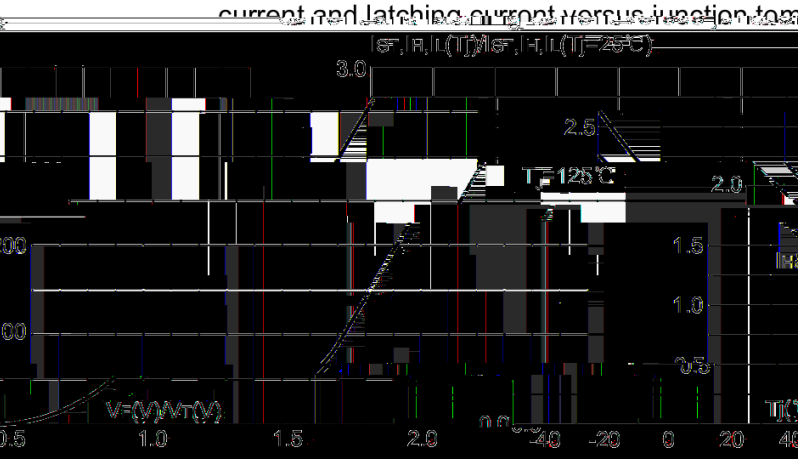



**FIG.5 Gate trigger characteristics**

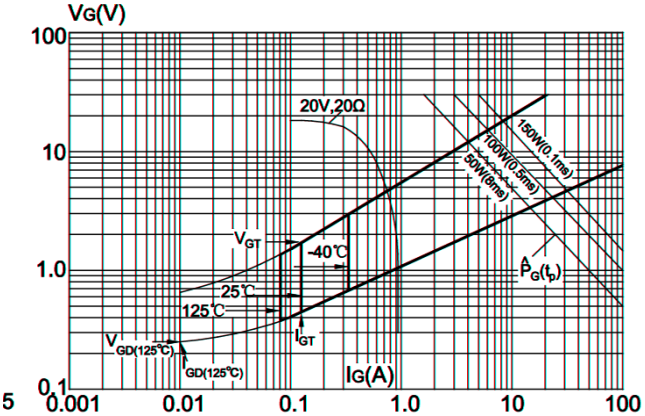
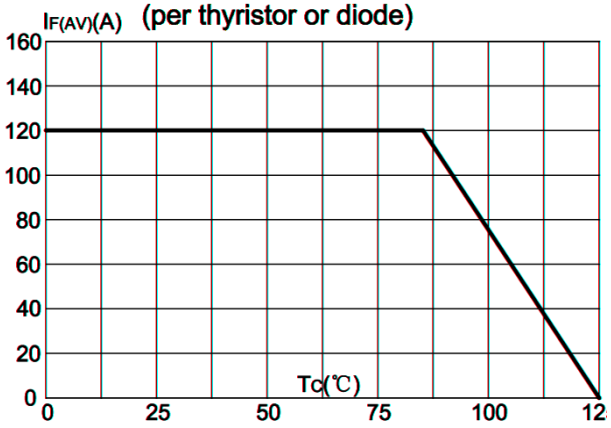
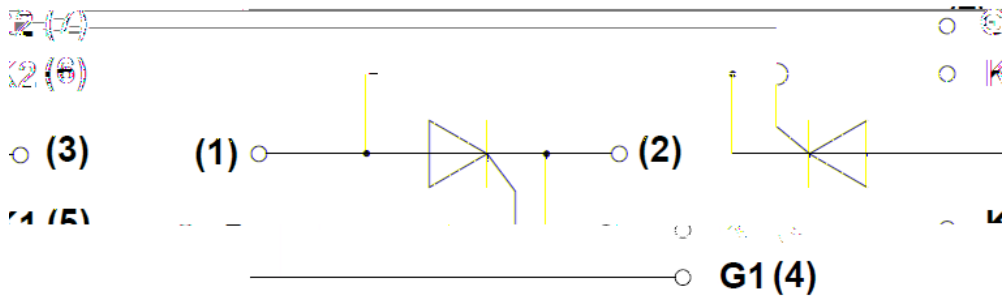
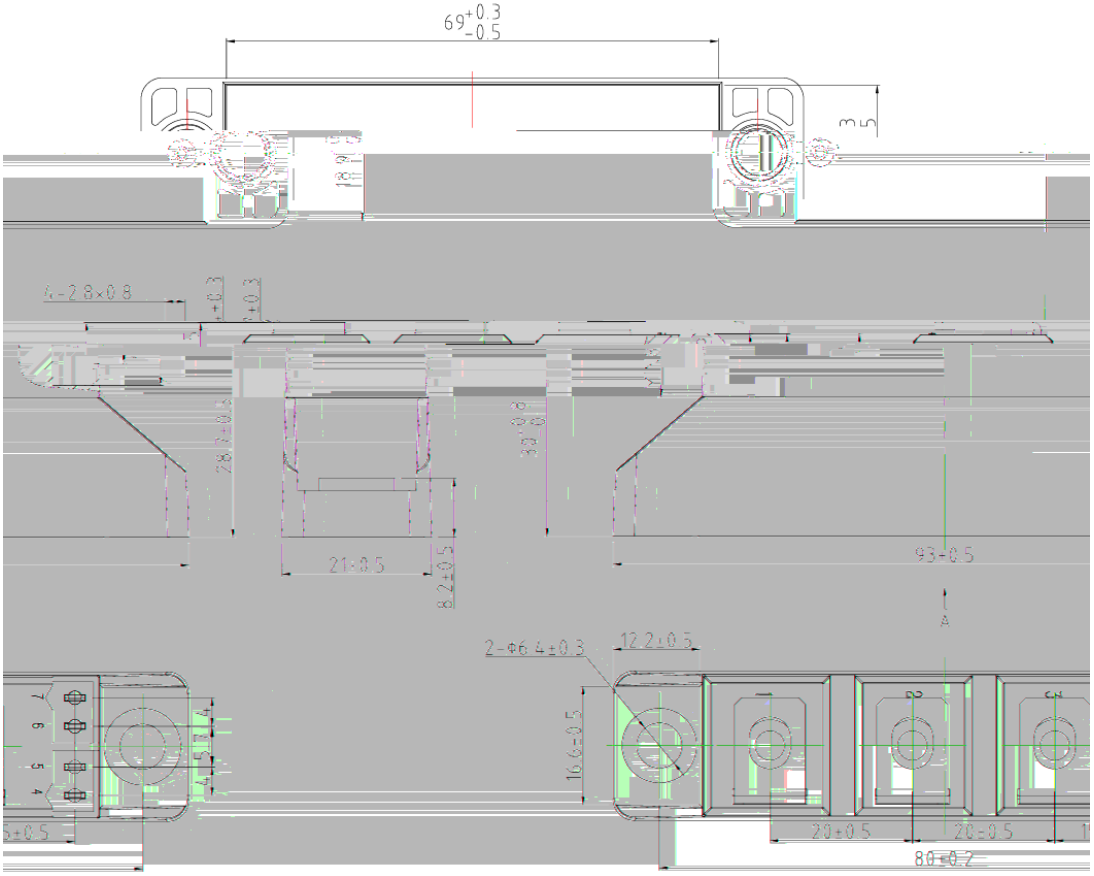



**FIG.6: Forward current vs. case temperature (per thyristor or diode)**




(3)
(1)
(2)
G1 (4)


69+0.3 -0.5
4-2.8×0.8
21±0.5
8.2±0.5
93±0.5
2-Φ6.4±0.3
12.2±0.5
16.6±0.5
20±0.5
20±0.5
80±0.2